

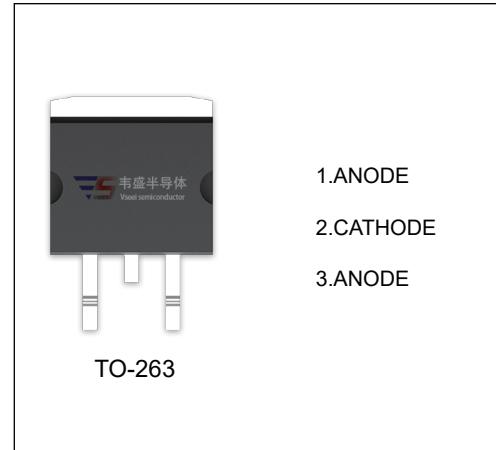
SBDB10100CT SCHOTTKY BARRIER RECTIFIER

MAIN CHARACTERISTICS

I_O	10 (2×5) A
V_{RRM}	100 V
T_j	150 °C
V_{F(typ)}	0.62V (@Ta=125°C)

FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{RRM}	Peak repetitive reverse voltage	100	V
V _{RWM}	Working peak reverse voltage		
V _R	DC blocking voltage	70	V
V _{R(RMS)}	RMS reverse voltage	10	A
I _O	Average rectified output current	120	A
I _{FSM}	Non-Repetitive peak forward surge current (8.3ms half sine wave)	2.0	°C/W
R _{θJC}	Thermal resistance from junction to case ,Tc=25°C	62.5	°C/W
R _{θJA}	Thermal resistance from junction to ambient	150	°C
T _j	Junction temperature	-55~+150	°C
T _{stg}	Storage temperature		

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	V _(BR)	I _R =0.1mA	100			V
Reverse current	I _R	V _R =100V	T _j =25°C	2.0	100	uA
			T _j =125°C	2.0		mA
Forward voltage	V _F	I _F =3A	T _j =25°C	0.71		V
			T _j =125°C	0.57		V
		I _F =5A	T _j =25°C	0.77	0.85	V
			T _j =125°C	0.63		V

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.

FIG.1: FORWARD CURRENT DERATING CURVE

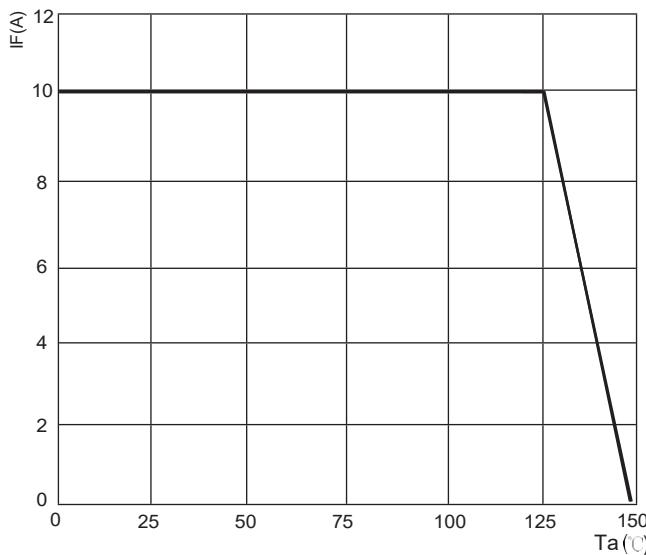


FIG.2: TYPICAL FORWARD CHARACTERISTICS

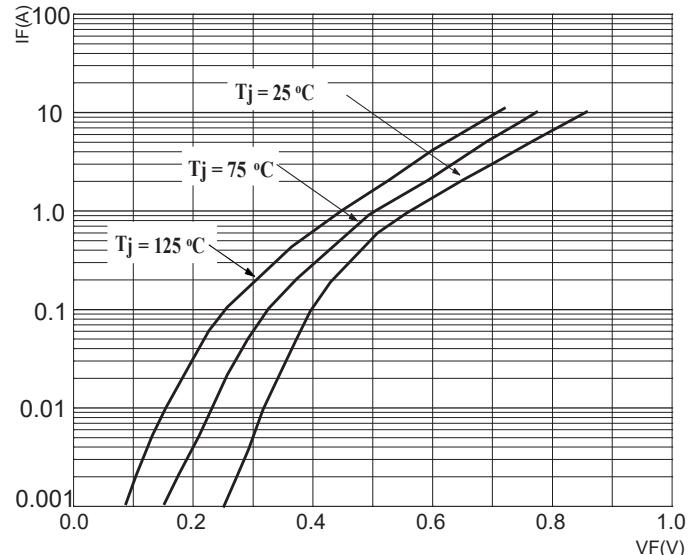


FIG.3: TOTAL CAPACITANCE DERATING CURVE

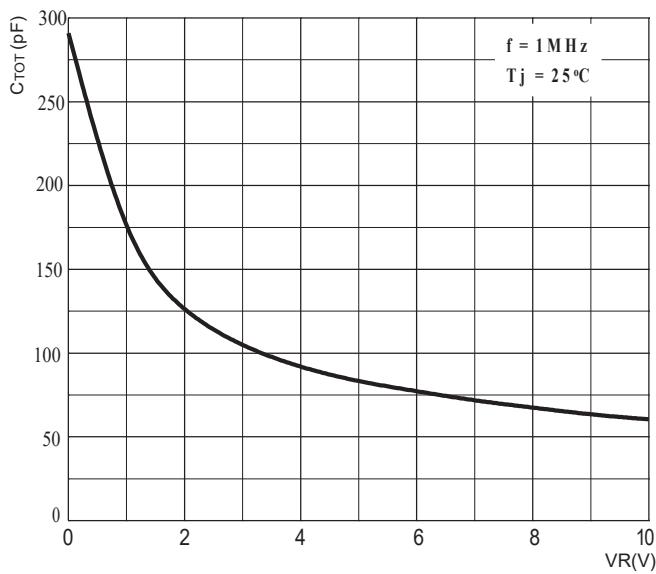


FIG.4: TYPICAL REVERSE CHARACTERISTICS

